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Cross-Line Characterization for Capacitive Cross Coupling in Differential Millimeter-Wave CMOS Amplifiers

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- Background & Motivation
- Cross-Line for Capacitive Cross Coupling
 - Characterization Structures
 - Method
- GSSG De-embedding Using Virtual-Thru
 - Results for De-embedding
- Results for Characterization
- Application Example on a Differential Amplifier







*57-66 GHz Unlicensed Frequency Band

- > 9 GHz Unlicensed band
 - Data rates up to 40 Gbps
- Large atmospheric attenuation
 - Secure Communication

8 Limited Communication Range

<u>*http://www.tele.soumu.go.jp/resource/e/search/share/2008/t3.pdf</u>





Direct Conversion RX on CMOS

- Single & differential RFamp I Mixer BBamp amplifiers ADC LO Buffer LNA Capacitive Cross-Coupling **Rx Input** Amplifier LO Buffer > Neutralization for ADC differential amplifiers **O** Mixer BBamp
 - > High gain
 - > Lower power consumption
 - Less Area
 - > Capacitive cross coupling amplifiers



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Capacitive Cross Coupling Amp.

- Important characteristic: Symmetry
- Asymmetrical crossing part
 - Amplitude imbalance
 - Phase imbalance
 - Unwanted mode conversions
- SNDR and EVM degradation









IN

OUT



Structures for Characterization

• Assuming symmetry and reciprocity



- Four unknowns for full characterization
 - Two four-port characterization structures





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Structures for Characterization

4 repeated



8 repeated



- > 4 and 8 repeated structure selected
 - > Easy calculation for fixture effects
- » Mixed-mode S-parameters
 - > Avoiding four-port T-parameters



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Method for Characterization

 Single-ended four-port S-parameters to mixed-mode S-parameters

$$[S_{MM}] = [M][S][M]^{-1} = \begin{bmatrix} S_{DD} & S_{DC} \\ S_{CD} & S_{CC} \end{bmatrix}$$

where;
$$[M] = \frac{1}{\sqrt{2}} \begin{bmatrix} I & -I \\ I & I \end{bmatrix}$$

- Symmetrical and reciprocal:
 - No mode conversion
- Two pure modes: two two-port networks
 Differential and common





Method of Characterization

■ Differential and common mode Sparameters → T-parameters



 $[T]_{4U,DD} = [T]_{LP,DD}[T]_{F,DD}[T]_{C,DD}{}^{4}[T]_{F,DD}[T]_{RP,DD}$ $[T]_{8U,DD} = [T]_{LP,DD}[T]_{F,DD}[T]_{C,DD}{}^{8}[T]_{F,DD}[T]_{RP,DD}$ $[T]_{PF,DD} = [T]_{4U,DD}[T]_{8U,DD}{}^{-1}[T]_{4U,DD}$



Similarly for common mode Pads has to be de-embedded



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GSSG Pad De-embedding



Solve for T-, and Π-model for two modes of pads





Results for De-embedding

Pad models: T-model and Π-model





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- Loss component and propagation constant independent of model
- Compared with single-ended transmission line results
 - Nearly the same (expected)

De-embedding from Fixture

- De-embed differential and common mode pad responses
 - From fixture results
- Solve for symmetrical fixture effects
 - For both left and right side
- De-embedding the fixture and pad Sparameters
 - Solve for one cross-line

$$[T]_{F,DD}^{-1}[T]_{LP,DD}^{-1}[T]_{4U,DD}[T]_{RP,DD}^{-1}[T]_{F,DD}^{-1} = [T]_{C,DD}^{4}$$

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Verification of Cross-Line

- Reconstruct the response of 8 repeated structure using:
 - Cross-line S-parameters
 - Fixture results
 - Pad results
- Comparison of model and measurement results are presented next

Results

Model and Measurements agree well up to 67 GHz

Application on Diff. Amp.

- An electrically symmetrical cross-line
 - Reduced amplitude and phase imbalance
- Characterization using two structures
- Mixed-mode S-parameters based calculations
 - Virtual-thru method for common and differential mode
- Model and measurement results for structure shows good agreement up to 67 GHz
- Amplifier model and measurements wellmatched up to 67 GHz

Thank you very much for your attention!

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